IN THE TITLE:

Please amend the title of the invention, in its entirety, so as to read as follows:

-- A SEMICONDUCTOR INTEGRATED CIRCUIT AND FABRICATION PROCESS HAVING COMPENSATED STRUCTURES TO REDUCE MANUFACTURING DEFECTS --.

IN THE SPECIFICATION:

Amend the specification as follows:

Page 1, paragraph starting at line 25, has been amended as indicated below:

In a flash memory, writing and erasing of information is done by injection and pulling out of hot-carriers to or from a floating-gate electrode through a tunneling insulation film. In this operation, a high voltage is required for producing hot-carriers. For this purpose, a boosting circuit is provided in a peripheral circuit that cooperates with a memory cell for boosting a power supply voltage. The transistor used in such a peripheral circuit is required to operate at high voltage.

IN THE CLAIMS:

Please **amend claims 16 and 17** as indicated below:

16. (Amended) A semiconductor integrated circuit, comprising:

a semiconductor substrate;